



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Kichiya TANINO et al.

Appln. No.: 09/771,556

Filed: January 30, 2001

For: SINGLE CRYSTAL SiC AND A
METHOD OF GROWING THE SAME

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) Art Unit: 1765
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) Ex: R.M. Kunemund
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TC 1700
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REPLY

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

The following remarks are offered in reply to the Office Action of December 16, 2002 and as an enclosure to the RCE being filed concurrently herewith.

REMARKS

Claims 1-10 were further examined and rejected as follows: (1) claims 1-6, 9 and 10 as unpatentable under 35 USC 103(a) over Tanino et al '279; and (2) claims 7 and 8 as unpatentable under 35 USC 103(a) also over Tanino et al '279.

While the rejections are separately stated, they are identical in that they both involve only Tanino et al '279.

In the previous Response it was noted that the invention claimed here and that disclosed in the Tanino et al '279 patent both have an α -SiC substrate and a polycrystalline β -SiC plate. It was noted, however, that the similarity stops there. According to the present invention,